## Shot noise near the unitary lim it of a K ondo quantum dot

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We exam ine the statistics of current uctuations in a junction with a quantum dot described by Kondo Ham iltonian. With the help of Keldysh technique we calculate shot noise as a function of applied voltage at zero temperature using the x-point Ham iltonian. These calculations are complementary to similar ones performed earlier ([1]) in the mean eld slave boson approximation. The results may be relevant for measurement of elective charge carriers.

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Current noise has been studied extensively in the context of mesoscopic systems in the last couple of decades [2]. The zero-frequency noise out of equilibrium (shot noise) can yield information on charge uctuations in such system s. We concentrate in the following on T = 0, where the therm alnoise vanishes and the only contribution to the current noise is shot noise. Due to the lack of a single accurate m ethod that can describe the K ondo system out of equilibrium in all regimes, dierent methods need to span all physically relevant regim es [1]. Here we consider the regime around the strongly interacting x point of K ondo H am iltonian where shot-noise measurem ents can provide inform ation about the charge of the carriers. The mean eld slave boson approximation which is usually applied to describe this regime [1, 3, 4] involves num erical calculations and it yields to the more precise perturbation theory expansion in the least irrelevant perturbations.

W e start w ith the K ondo H am iltonian for quantum dot in the junction H = H  $_{\rm L}$  + H  $_{\rm R}$  + H  $_{\rm J}$  where

$$H_{J} = \int_{0}^{X} J \circ C^{Y} (0) \left(\frac{1}{4} ; \circ + Ss \circ) C \circ \circ (0) (1)\right)$$

The rst two terms correspond to non-interacting electrons in the two leads

$$H_{L(R)} = X_{L(R)k} c_{L(R);k}^{y} c_{L(R);k} c_{L(R);k}$$
(2)

where c  $_{;k}$ ,  $_{k}$  are the electron eld operator and the electron energy of a lead. Index = L;R indicates left (right) lead. We assume that the leads are do-biased by applied voltage V. Here s is the one half spin matrix which acts on spin index of electron operators and S is the spin operator of the dot. The potential scattering is represented by the rst term in the brackets. We consider the case with the same dispersion law in both leads. Near the unitary limit we follow [5] and map the transport through the dot into a scattering problem. For this purpose, it is convenient to use the basis of s and p scattering states rather than that of the left-lead and right-lead states. At V = 0 the p states are decoupled from the

dot. For non-zero voltage the p-states are not decoupled, however, in the lim it of low voltages V <<  $T_K$  the s, p basis is important. Indeed, in this regime the dot is described by strongly interacting x-point with many body state (b). Before scattering the phases of both states, b and s-state, coincide, while passing the scattering region b state acquires only an extra phase compared to that of s-state. Then the x-point Ham iltonian can be written [5, 6, 7] in the new basis (b  $_{;k}$ ; a  $_{;k}$ ) (here a stands for p-states) as H = H  $_0$  + H  $_s$  + H  $_{int}$ 

$$H_{0} = \frac{X}{k} \left(b^{y}_{;k} b_{;k} a^{y}_{;k} a_{;k}\right) + \frac{V}{2} \frac{X}{k} \left(b^{y}_{;k} a_{;k} + a^{y}_{;k} b_{;k}\right) + \frac{a}{T_{K}} \frac{X}{k_{;k}^{0}} \left(k + k^{0} b^{y}_{;k} b_{;k}\right)$$

$$(3)$$

$$H_{int} = \frac{b}{2T_{K}} b_{n}^{y} b_{n} b_{\#}^{y} b_{\#}$$
 (4)

where b = 2a and a = 1=(2 ) [6] and b =  $\frac{P}{k}$  b, the K ondo temperature  $T_K$  is the only energy scale of the xed-point H am iltonian.

Current noise is de ned as

$$S(t) < I(t)I(0) > < I >^{2};$$
 (5)

where the current operator requires a form

$$I = \frac{2e^{2}V}{h} \frac{ie}{h} \frac{a}{2} \frac{X}{T_{K}} (_{k} + _{k^{0}})$$

$$(b^{Y}_{jk^{0}} a_{jk} a_{jk} a^{Y}_{jk} b_{jk^{0}})$$

$$+ \frac{ie}{h} \frac{b}{2^{2}T_{K}} X$$

$$(b^{Y} a a^{Y} b) n \qquad (6)$$

and  $n = b^y b$ , = .

The noise power can be represented as a sum of two terms  $S = S_{\text{scat}} + S_{\text{int}}$  related, respectively , to the scattering part of the H am iltonian H  $_{\text{S}}$  and to the interaction part H  $_{\text{int}}$ .

$$S_{\text{scat}}(t; t^{0}) = \frac{e^{2}}{h} \frac{a^{2}}{4^{2}T_{K}^{2}} X_{k_{1}; i} (k_{1} + k_{1}) (k_{0} + k_{1}) (k_{0} + k_{1}) (k_{0}) + k_{1}^{0}) (k_{1}^{y} + k_{1}) (k_{1}^{y} + k_{1}) (k_{1}^{y} + k_{1}^{y} + k_{1}^{y}) (k_{1}^{y} + k_{1}^{y} + k_{1}^{y} + k_{1}^{y}) (k_{1}^{y} + k_{1}^{y} + k_{1}^{y}) (k_{1}^{y} + k_{1}^{y} + k_{1}^{y} + k_{1}^{y}) (k_{1}^{y} + k_{1}^{y} + k_{1}^{y} + k_{1}^{y} + k_{1}^{y} + k_{1}^{y} + k_{1}^{y}) (k_{1}^{y} + k_{1}^{y} +$$

Here subscripts t;  $t^0$  represent time dependence of operators. We can write the right hand side of  $S_{\rm scat}$  and  $S_{\rm int}$  as a time ordering product in Keldysh space. (This can be simply done by assigning Keldysh indices 2 and 1 to operators that depends on t;  $t^0$ , correspondingly. Then it is possible to express the result in terms of G reen's functions of H $_0$  Ham iltonian. Let us perform the Fourier transform of equations (7,8). Then for zero frequency noise (after sum ming over spin projections) we immediately get

$$S_{\text{scat}} = \frac{e^{2}}{h} \frac{a^{2}}{^{2}T_{K}^{2}} \frac{Z}{2} \frac{d!}{k_{1}!} \frac{X}{(k_{1} + k_{1})^{2}} \left[g_{d}^{21}(k_{1}!)g_{d}^{12}(k_{1}!)$$

G reen functions in the space of a;b states can be written as a matrix g with diagonal and o -diagonal entries each being K eldysh matrices.

$$g_d^{ij}(t;t^0) = i < Tb^i(t)b^{yj}(t^0) >$$
 (11)

$$g_{off}^{ij}(t;t^0) = i < Tb^i(t)a^{yj}(t^0) >$$
 (12)

Explicitly, they acquire a form

$$g^{12}(k!) = f(_{k})(g^{R}(k!) g^{A}(k!))$$
(13)
$$g^{21}(k!) = (1 f(_{k}))(g^{R}(k!) g^{A}(k!))$$
(14)
$$g^{R}(k!) g^{A}(k!) = i[(! _{k} eV=2) + (! _{k} + eV=2)]\hat{I} + [(! _{k} eV=2) (! _{k} + eV=2)]\hat{I}$$
(15)
$$g^{ij}(!) = d_{k}g^{ij}(k!)$$
(15)
$$g^{12}_{off}(!) = g^{21}_{off}(!) = i[f(! eV=2) f(! + eV=2)]$$

$$g^{12}(!) = g^{21}_{d}(!) + 2 i$$

$$= i[f(! eV=2) + f(! + eV=2)]$$

W ith the help of these functions we get:

$$S_{\text{scat}} = \frac{e^{2}}{h} \frac{a^{2}8^{2}}{T_{K}^{2}}^{Z} \quad d! \; !^{2} \left[ f \left( ! - \frac{eV}{2} \right) \left( 1 - f \left( ! + \frac{eV}{2} \right) \right) \right]$$

$$+ f \left( ! + \frac{eV}{2} \right) \left( 1 - f \left( ! - \frac{eV}{2} \right) \right) =$$

$$= \frac{2e^{2}}{h} \left( \frac{a^{2}}{3} \right) V \frac{\left( eV \right)^{2}}{T_{K}^{2}} \qquad (16)$$

$$S_{\text{int}} = \frac{e^{2}}{h} \frac{b^{2}}{8T_{K}^{2}} \quad d!_{1} d!_{2} d!_{3} \left[ (2 - F_{+} (!_{1}))F_{+} (!_{2}) + F_{-} (!_{1})F_{+} (!_{2}) \right]$$

$$+ F_{-} (!_{1})F_{-} (!_{2}) \left( (2 - F_{+} (!_{1}))F_{-} (!_{2}) + F_{-} (!_{1})F_{+} (!_{2}) \right) \left( (2 - F_{+} (!_{3}))F_{+} (!_{1} - !_{2} + !_{3}) + F_{-} (!_{3})F_{+} (!_{1} - !_{2} + !_{3}) \right)$$

where F (!) = f(! eV=2) f(! + eV=2).

Perform ing the triple integration (at T ! 0) we obtain part of the noise  $S_{\rm int}$  which is induced by interaction H am iltonian H  $_{\rm int}$ . Thus the total shot noise power in the lim it of sm all voltages eV <<  $T_{\rm K}$  acquires a form

$$S_{int} = \frac{e^2 V}{h}^2 \left(\frac{3}{2}b^2 + \frac{2a^2}{3}\right) \frac{(eV)^2}{T_K^2}$$
 (17)

For completeness we also calculate nonlinear conductance [5, 6]. Similarly to the noise the current consist of to parts  $j = j_{scat} + j_{int}$ , where  $j_{scat}$  is the scattering part

$$j_{\text{scat}} = \frac{e}{h} < \hat{T} [H_s; N_R]_t^1 dt^0 \frac{i}{z} H_s^i(t^0) >$$
 (18)

and jint interacting part

$$j_{int} = \frac{e}{h} < \hat{T} H_{int}; N_R l_t^1 dt^0 l_{int}^1 H_{int}^1 (t^0) >$$
 (19)

Here  $\hat{T}$  represents time-ordering operator. We also explicitly introduced Keldysh indices i=1;2 and dened i=1;2=1.

Thus for the scattering part of the current we obtain

$$j_{\text{scat}} = \frac{e}{h} \frac{a^2}{2T_K^2} \frac{Z}{2} \frac{d!}{2} \frac{X}{k_{i}k_{1}} (k_{i} + k_{1})^2 (f(k_{i}))$$

$$f(k_{1})g_{d}^{\text{dif}}(k_{1}!)g_{off}^{\text{dif}}(k_{1}!) \qquad (20)$$

where  $g^{\rm dif}=g^R-g^A$  . The frequency integration and momentum summation can be easily done with the result:

$$j_{\text{scat}} = \frac{2e^2}{h} \frac{a^2}{3} \left(\frac{eV}{T_K}\right)^2 V$$
 (21)

For interacting part we have

$$j_{\text{int}} = \frac{2e^2}{h} \frac{b^2}{3} \frac{2}{4} (\frac{eV}{T_K})^2 V$$
 (22)

Thus total nonlinear conductance at zero temperature and in the case of small voltages eV <<  $T_{\rm K}\,$  acquires a form

$$= \frac{2e^2}{h} [1 \quad {}^{2} (a^2 + b^2 \frac{5}{4}) (\frac{eV}{T_K})^2]$$
 (23)

This result is in agreement with that obtained in [6].

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